

# The Doping of Semiconductors

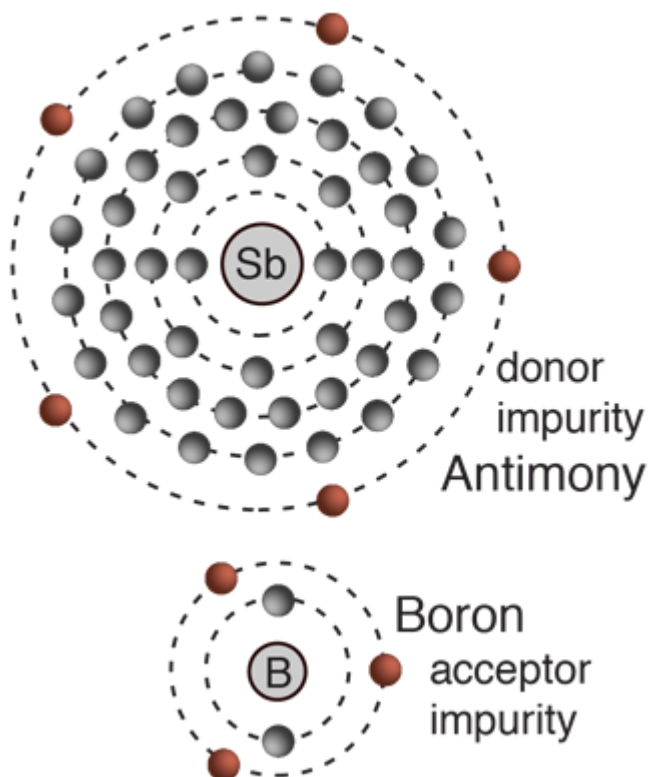
The addition of a small percentage of foreign atoms in the regular [crystal lattice](#) of silicon or germanium produces dramatic changes in their electrical properties, producing [n-type](#) and [p-type](#) semiconductors.

## Pentavalent impurities

Impurity atoms with 5 [valence electrons](#) produce n-type semiconductors by contributing extra electrons.

Antimony  
Arsenic  
Phosphorous

Boron  
Aluminum  
Gallium



## Trivalent impurities

Impurity atoms with 3 valence electrons produce p-type semiconductors by producing a "[hole](#)" or electron deficiency.

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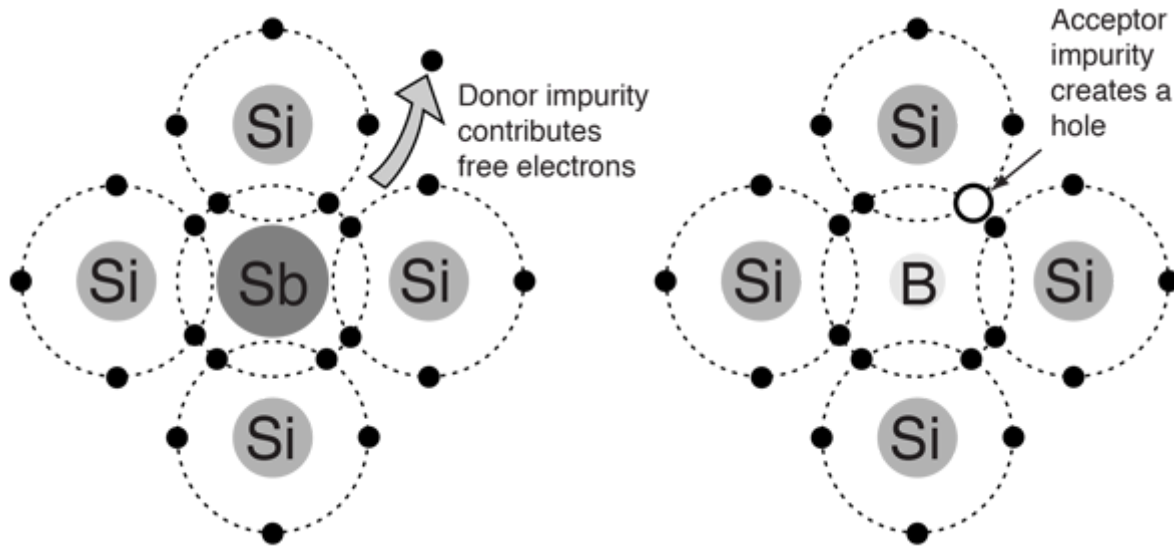
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# P- and N- Type Semiconductors

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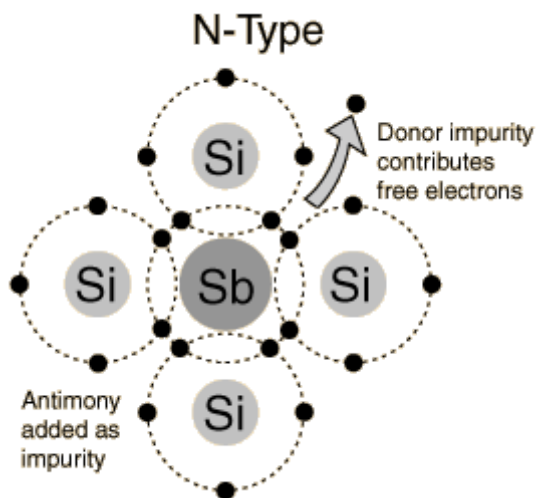
Click on either for further information.

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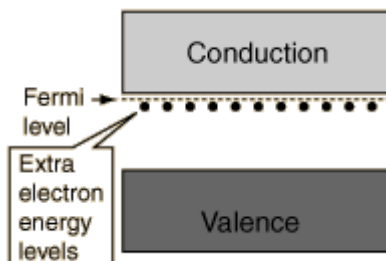
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## N-Type Semiconductor



The addition of pentavalent [impurities](#) such as antimony, arsenic or phosphorus contributes free electrons, greatly increasing the conductivity of the [intrinsic semiconductor](#). Phosphorus may be added by diffusion of phosphine gas ( $\text{PH}_3$ ).



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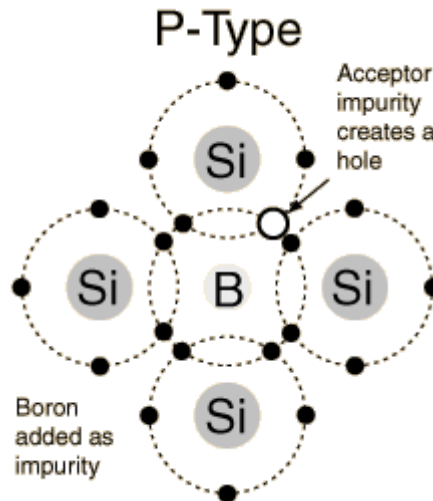
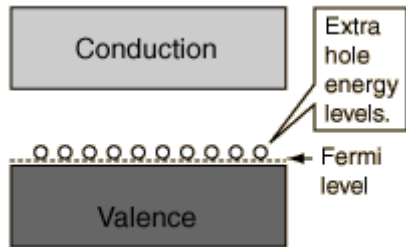
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# P-Type Semiconductor

The addition of trivalent [impurities](#) such as boron, aluminum or gallium to an [intrinsic semiconductor](#) creates deficiencies of valence electrons, called "holes". It is typical to use  $B_2H_6$  diborane gas to diffuse boron into the silicon material.



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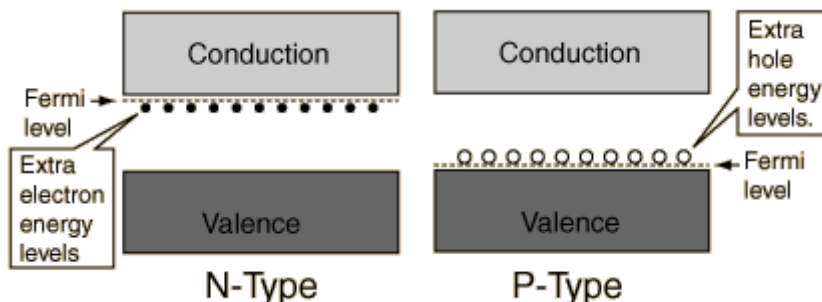
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## Bands for Doped Semiconductors

The application of [band theory](#) to [n-type](#) and [p-type](#) semiconductors shows that extra levels have been added by the impurities. In n-type material there are electron energy levels near the top of the band gap so that they can be easily excited into the conduction band. In p-type material, extra holes in the band gap allow excitation of valence band electrons, leaving mobile holes in the valence band.



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